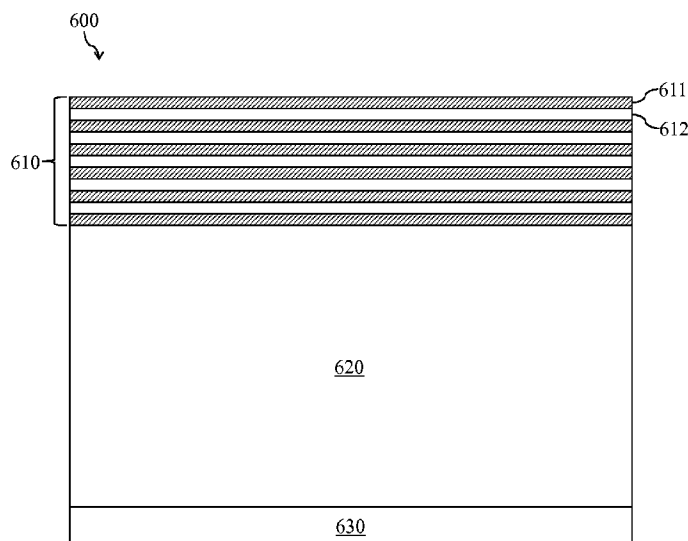




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(72) Inventeurs/Inventors:
HENDRIX, KAREN DENISE, US;
BRADLEY, RICHARD A., JR., US;
GRIGONIS, MARIUS, US;
OCKENFUSS, GEORG, US
(73) Propriétaire/Owner:
VIAVI SOLUTIONS INC., US
(74) Agent: GOWLING WLG (CANADA) LLP

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(57) Abrégé/Abstract:

An optical filter having a passband at least partially overlapping with a wavelength range of 800 nm to 1100 nm is provided. The optical filter includes a filter stack formed of hydrogenated silicon layers and lower-refractive index layers stacked in alternation. The hydrogenated silicon layers each have a refractive index of greater than 3 over the wavelength range of 800 nm to 1100 nm and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1 100 nm.

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- (71) Applicant: **JDS UNIPHASE CORPORATION** [US/US];
430 N. McCarthy Boulevard, Milpitas, CA 95035 (US).
- (72) Inventors: **HENDRIX, Karen, Denise**; 419 Countryside
Circle, Santa Rosa, CA 95401 (US). **BRADLEY, Richard,
A., Jr.**; 1436 Lawrence Way, Santa Rosa, CA 95401 (US).
GRIGONIS, Marius; 2060 Leonard Ave., Santa Rosa, CA
95405 (US).
- (74) Agent: **PEQUIGNOT, Matthew, A.**; Pequignot + Myers
LLC, 90 North Coast Highway 101, Suite 315, Encinitas,
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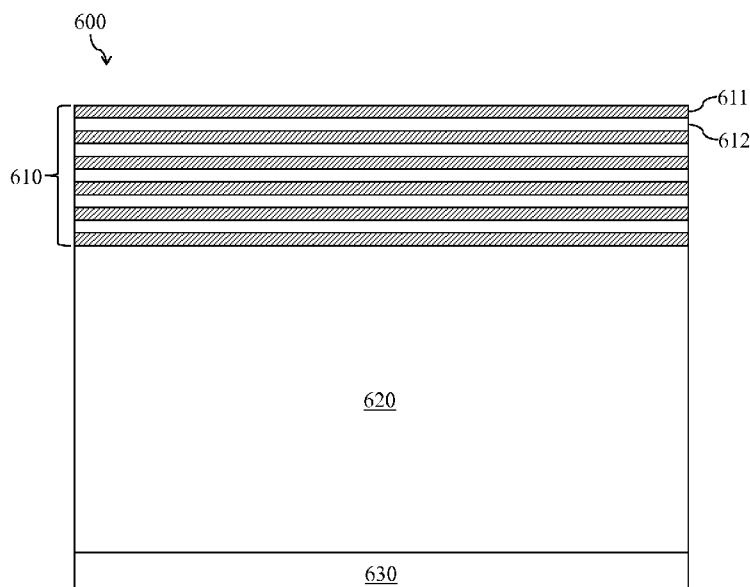


FIG. 6

(57) Abstract: An optical filter having a passband at least partially overlapping with a wavelength range of 800 nm to 1100 nm is provided. The optical filter includes a filter stack formed of hydrogenated silicon layers and lower-refractive index layers stacked in alternation. The hydrogenated silicon layers each have a refractive index of greater than 3 over the wavelength range of 800 nm to 1100 nm and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1 100 nm.

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OPTICAL FILTER AND SENSOR SYSTEM

TECHNICAL FIELD OF THE INVENTION

[0001] The present invention relates to optical filters and to sensor systems comprising optical filters. More particularly, the present invention relates to optical filters including hydrogenated silicon layers and to sensor systems comprising such optical filters.

BACKGROUND OF THE INVENTION

[0002] In a typical gesture-recognition system, a light source emits near-infrared light towards a user. A three-dimensional (3D) image sensor detects the emitted light that is reflected by the user to provide a 3D image of the user. A processing system then analyzes the 3D image to recognize a gesture made by the user.

[0003] An optical filter, more specifically, a bandpass filter, is used to transmit the emitted light to the 3D image sensor, while substantially blocking ambient light. In other words, the optical filter serves to screen out ambient light. Therefore, an optical filter having a narrow passband in the near-infrared wavelength range, *i.e.*, 800 nm to 1100 nm, is required. Furthermore, the optical filter must have a high transmittance level within the passband and a high blocking level outside of the passband.

[0004] Conventionally, the optical filter includes a filter stack and a blocking stack, coated on opposite surfaces of a substrate. Each of the stacks is formed of high-refractive-index layers and low-refractive-index layers stacked in alternation. Different oxides are, generally, used for the high-refractive-index layers and the low-refractive-index layers, such as TiO_2 , Nb_2O_5 , Ta_2O_5 , SiO_2 , and mixtures thereof. For example, some conventional optical filters include a $\text{TiO}_2/\text{SiO}_2$ filter stack and a $\text{Ta}_2\text{O}_5/\text{SiO}_2$ blocking stack, in which the high-refractive index layers are composed of TiO_2 or Ta_2O_5 , respectively, and the low-refractive-index layers are composed of SiO_2 .

[0005] In a first conventional optical filter designed to transmit light in a wavelength range of 829 nm to 859 nm over an incidence angle range of 0° to 30° , the filter stack includes 71 layers, the blocking stack includes 140 layers, and the total coating thickness is about 24 μm . Transmission spectra 100 and 101 at incidence angles of 0° and 30° , respectively, for this optical

filter are plotted in FIG. 1. In a second conventional optical filter designed to transmit light at a wavelength of 825 nm over an incidence angle range of 0° to 20°, the filter stack includes 43 layers, the blocking stack includes 82 layers, and the total coating thickness is about 14 μm . Transmission spectra 200 and 201 at incidence angles of 0° and 20°, respectively, for this optical filter are plotted in FIG. 2. In a third conventional optical filter designed to transmit light in a wavelength range of 845 nm to 865 nm over an incidence angle range of 0° to 24°, the filter stack includes 77 layers, the blocking stack includes 148 layers, and the total coating thickness is about 26 μm . Transmission spectra 300 and 301 at incidence angles of 0° and 24°, respectively, for this optical filter are plotted in FIG. 3.

[0006] With reference to FIGS. 1–3, the first, second, and third conventional optical filters, generally, have a high transmittance level within the passband and a high blocking level outside of the passband. However, the center wavelength of the passband undergoes a relatively large shift with change in incidence angle. Consequently, the passband must be relatively wide to accept light over the required incidence angle range, increasing the amount of ambient light that is transmitted and reducing the signal-to-noise ratio of systems incorporating these conventional optical filters. Furthermore, the large number of layers in the filter stacks and blocking stacks increases the expense and coating time involved in fabricating these conventional optical filters. The large total coating thickness also makes these conventional optical filters difficult to pattern, *e.g.*, by photolithography.

[0007] To enhance the performance of the optical filter in the gesture-recognition system, it would be desirable to reduce the number of layers, the total coating thickness, and the center-wavelength shift with change in incidence angle. One approach is to use a material having a higher refractive index than conventional oxides over the wavelength range of 800 nm to 1100 nm for the high-refractive-index layers. In addition to a higher refractive index, the material must also have a low extinction coefficient over the wavelength range of 800 nm to 1100 nm in order to provide a high transmittance level within the passband.

[0008] The use of hydrogenated silicon (Si:H) for high-refractive-index layers in optical filters is disclosed by Lairson, et al. in an article entitled "Reduced Angle-Shift Infrared Bandpass Filter Coatings" (Proceedings of the SPIE, 2007, Vol. 6545, pp. 65451C-1–65451C-5),

and by Gibbons, et al. in an article entitled "Development and Implementation of a Hydrogenated a-Si Reactive Sputter Deposition Process" (Proceedings of the Annual Technical Conference, Society of Vacuum Coaters, 2007, Vol. 50, pp. 327–330). Lairson, et al. disclose a hydrogenated silicon material having a refractive index of 3.2 at a wavelength of 1500 nm and an extinction coefficient of less than 0.001 at wavelengths of greater than 1000 nm. Gibbons, et al. disclose a hydrogenated silicon material, produced by alternating current (AC) sputtering, having a refractive index of 3.2 at a wavelength of 830 nm and an extinction coefficient of 0.0005 at a wavelength of 830 nm. Unfortunately, these hydrogenated silicon materials do not have a suitably low extinction coefficient over the wavelength range of 800 nm to 1100 nm.

SUMMARY OF THE INVENTION

[0009] Accordingly, the present invention relates to an optical filter having a passband at least partially overlapping with a wavelength range of 800 nm to 1100 nm, comprising: a filter stack including: a plurality of hydrogenated silicon layers each having a refractive index of greater than 3 over the wavelength range of 800 nm to 1100 nm and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1100 nm; and a plurality of lower-refractive-index layers each having a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm, stacked in alternation with the plurality of hydrogenated silicon layers.

[0010] The present invention also relates to a sensor system comprising: a light source for emitting light at an emission wavelength in a wavelength range of 800 nm to 1100 nm; an optical filter having a passband including the emission wavelength and at least partially overlapping with the wavelength range of 800 nm to 1100 nm, disposed to receive the emitted light, for transmitting the emitted light while substantially blocking ambient light, comprising: a filter stack including: a plurality of hydrogenated silicon layers each having a refractive index of greater than 3 over the wavelength range of 800 nm to 1100 nm and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1100 nm; and a plurality of lower-refractive-index layers each having a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm, stacked in alternation with the plurality of hydrogenated silicon layers; and a sensor, disposed to receive the emitted light after transmission by the optical filter, for detecting the emitted light.

BRIEF DESCRIPTION OF THE DRAWINGS

[0011] The present invention will be described in greater detail with reference to the accompanying drawings wherein:

[0012] FIG. 1 is a plot of transmittance spectra at incidence angles of 0° and 30° for a first conventional optical filter;

[0013] FIG. 2 is a plot of transmittance spectra at incidence angles of 0° and 20° for a second conventional optical filter;

[0014] FIG. 3 is a plot of transmittance spectra at incidence angles of 0° and 24° for a third conventional optical filter;

[0015] FIG. 4 is a schematic illustration of a sputter-deposition system;

[0016] FIG. 5A is a plot of transmittance spectra for 1500-nm-thick silicon layers deposited in the presence and absence of hydrogen;

[0017] FIG. 5B is a plot of the absorption-edge wavelength at a transmittance level of 50 % against hydrogen flow rate for hydrogenated silicon (Si:H) layers before and after an annealing step;

[0018] FIG. 5C is a plot of refractive index at wavelengths of 800 nm to 1120 nm against hydrogen flow rate for hydrogenated silicon layers;

[0019] FIG. 5D is a plot of absorption coefficient at wavelengths of 800 nm to 880 nm against hydrogen flow rate for hydrogenated silicon layers;

[0020] FIG. 6 is a schematic illustration of a cross-section of an optical filter according to the present invention;

[0021] FIG. 7A is a table comparing properties of the first conventional optical filter of FIG. 1 and a first exemplary optical filter according to the present invention;

[0022] FIG. 7B is a table listing layer numbers, materials, and thicknesses for the antireflective (AR) coating of the first exemplary optical filter;

[0023] FIG 7C is a table listing layer numbers, materials, and thicknesses for the filter stack of the first exemplary optical filter;

[0024] FIG. 7D is a plot of transmittance spectra at incidence angles of 0° and 30° for the first exemplary optical filter;

[0025] FIG. 7E is a plot of transmittance spectra at incidence angles of 0° and 30° for an optical filter analogous to the first exemplary optical filter, but including an Si/SiO₂ filter stack;

[0026] FIG. 8A is a table comparing properties of the second conventional optical filter of FIG. 2 and a second exemplary optical filter according to the present invention;

[0027] FIG 8B is a table listing layer numbers, materials, and thicknesses for the filter stack of the second exemplary optical filter;

[0028] FIG. 8C is a plot of transmittance spectra at incidence angles of 0° and 20° for the second exemplary optical filter;

[0029] FIG. 8D is a plot of transmittance spectra at incidence angles of 0° and 20° for an optical filter analogous to the second exemplary optical filter, but including an Si/SiO₂ filter stack;

[0030] FIG 9A is a table listing layer numbers, materials, and thicknesses for the filter stack of a third exemplary optical filter according to the present invention;

[0031] FIG. 9B is a plot of transmittance spectra at incidence angles of 0° and 40° for the third exemplary optical filter; and

[0032] FIG. 10 is a block diagram of a sensor system according to the present invention.

DETAILED DESCRIPTION OF THE INVENTION

[0033] The present invention provides an optical filter including hydrogenated silicon (Si:H) layers, which is particularly suitable for use in a sensor system, such as a proximity sensor system, a three-dimensional (3D) imaging system, or a gesture-recognition system.

[0034] The optical filter of the present invention uses an improved hydrogenated silicon material, which has both a high refractive index and a low absorption coefficient over a wavelength range of 800 nm to 1100 nm, *i.e.*, in the near-infrared wavelength range. Typically, the hydrogenated silicon material is amorphous. The hydrogenated silicon material is, preferably, produced by pulsed direct current (DC) sputtering. A sputter-deposition system suitable for producing the hydrogenated silicon material is described in U.S. Patent No. 8,163,144 to Tilsch, et al., issued on April 24, 2012.

[0035] With reference to FIG. 4, a typical sputter-deposition system 400 used to produce the hydrogenated silicon material includes a vacuum chamber 410, a substrate 420, a cathode 430, a cathode power supply 440, an anode 450, a plasma activation source (PAS) 460, and a PAS power supply 470. The cathode 430 is powered by the cathode power supply 440, which is a pulsed DC power supply. The PAS 460 is powered by the PAS power supply 470, which is a radio frequency (RF) power supply.

[0036] The cathode 430 includes a silicon target 431, which is sputtered in the presence of hydrogen (H_2), as well as an inert gas such as argon, to deposit the hydrogenated silicon material as a layer on the substrate 420. The inert gas is introduced into the vacuum chamber 410 through the anode 450 and the PAS 460. Alternatively, the walls of the vacuum chamber 410 may serve as the anode, and the inert gas may be introduced at a different location.

[0037] Hydrogen is introduced into the vacuum chamber 410 through the PAS 460, which serves to activate the hydrogen. Activated hydrogen is more chemically reactive and is, therefore, more likely to create Si-H bonds, which are thought to be responsible for the optical properties of the hydrogenated silicon material. The PAS 460 is located very close to the cathode 430, allowing the PAS plasma and the cathode plasma to overlap. Both atomic and molecular species of activated hydrogen are believed to be present in the plasmas. The use of the PAS 460 allows the hydrogenated silicon layer to be deposited at a relatively high deposition rate with a relatively low hydrogen content. Typically, the hydrogenated silicon layer is deposited at a deposition rate of 0.05 nm/s to 1.2 nm/s, preferably, at a deposition rate of about 0.8 nm/s. Alternatively, the cathode plasma alone may be used for hydrogen activation.

[0038] The optical properties of the hydrogenated silicon material depend primarily on the hydrogen content in the vacuum chamber 410 and, therefore, on the hydrogen flow rate. However, they are also influenced by other parameters, such as the flow rate of the inert gas, the PAS power level, the cathode power level, and the deposition rate.

[0039] FIG. 5A shows transmission spectra 500 and 501 for 1500-nm-thick silicon layers deposited in the presence of hydrogen, at a hydrogen flow rate of 139 sccm, and in the absence of hydrogen, respectively. The silicon layer deposited in the presence of hydrogen, *i.e.*, the hydrogenated silicon layer, has a significantly higher transmittance level over the wavelength range of 800 nm to 1100 nm.

[0040] FIG. 5B shows curves 510 and 511 of the absorption-edge wavelength at a transmittance level of 50 % against hydrogen flow rate for hydrogenated silicon layers before and after an annealing step, respectively. For the as-deposited hydrogenated silicon layers, the absorption-edge wavelength decreases with increasing hydrogen flow rate. Generally, the absorption-edge wavelength varies approximately logarithmically with hydrogen flow rate. The absorption-edge wavelength is decreased further by the annealing step, which was carried out at a temperature of about 300 °C for about 60 minutes. Typically, when an optional post-coating annealing step is performed, the hydrogenated silicon layers are annealed at a temperature of up to 350 °C for up to 120 minutes, preferably, at a temperature of 250 °C to 350 °C for 30 to 90 minutes. In some instances, more than one annealing step may be performed.

[0041] Thus, the absorption-edge wavelength of the hydrogenated silicon material can be tuned by adjusting the hydrogen flow rate and, optionally, by annealing. Likewise, the refractive index and the absorption coefficient of the hydrogenated silicon material can also be tuned by adjusting the hydrogen flow rate and, optionally, by annealing. Typically, the hydrogenated silicon layers are deposited with a hydrogen flow rate of greater than 80 sccm, preferably, a hydrogen flow rate of about 80 sccm. However, it should be noted that the hydrogen content associated with this flow rate will depend on the pumping speed of the vacuum system.

[0042] FIG. 5C shows a plot of refractive index at wavelengths of 800 nm to 1120 nm against hydrogen flow rate for as-deposited hydrogenated silicon layers. The refractive index decreases with increasing hydrogen flow rate. Generally, the refractive index varies

approximately linearly with hydrogen flow rate. In particular, the refractive index of the hydrogenated silicon layer produced at a hydrogen flow rate of 80 sccm is greater than 3.55 over the wavelength range of 800 nm to 1120 nm.

[0043] FIG. 5D shows a plot of absorption coefficient at wavelengths of 800 nm to 880 nm against hydrogen flow rate for as-deposited hydrogenated silicon layers (the absorption coefficient is less than 0.0001 at wavelengths of 920 nm to 1120 nm). The absorption coefficient decreases with increasing hydrogen flow rate. Generally, the absorption coefficient varies approximately exponentially with hydrogen flow rate. In particular, the absorption coefficient of the hydrogenated silicon layer produced at a hydrogen flow rate of 80 sccm is less than 0.0004 over the wavelength range of 800 nm to 1120 nm.

[0044] The improved hydrogenated silicon material, tuned to have suitable optical properties, is used in the optical filter of the present invention. With reference to FIG. 6, the optical filter 600 includes a filter stack 610, which is disposed on a first surface of a substrate 620. In most instances, the substrate 620 is a free-standing substrate, typically, a glass substrate, *e.g.*, a borofloat glass substrate. Alternatively, the substrate 620 may be a sensor or another device. When the substrate 620 is a free-standing substrate, an antireflective (AR) coating 630 is often disposed on a second surface of the substrate 620 opposite the first surface. Typically, the AR coating 630 is a multilayer interference coating, *e.g.*, a $\text{Ta}_2\text{O}_5/\text{SiO}_2$ coating. Also typically, the AR coating 630 has a thickness of 0.1 μm to 1 μm .

[0045] The filter stack 610 includes a plurality of hydrogenated silicon layers 611, which serve as higher-refractive-index layers, and a plurality of lower-refractive-index layers 612 stacked in alternation. Usually, the filter stack 610 consists of a plurality of hydrogenated silicon layers 611 and a plurality of lower-refractive-index layers 612 stacked in a sequence of $(\text{H/L})_n$, $(\text{H/L})_n\text{H}$, or $\text{L}(\text{H/L})_n$. Typically, the filter stack 610 includes a total of 10 to 100 layers, *i.e.*, $5 \leq n \leq 50$. Also typically, the hydrogenated silicon layers 611 and the lower-refractive-index layers 612 each have a thickness of 3 nm to 300 nm, and the filter stack 610 has a thickness of 1 μm to 10 μm . Generally, the layer numbers and thicknesses are selected according to a particular optical design. Preferably, the optical filter 600 has a total coating thickness, *i.e.*, the thickness of the filter stack 610 and the AR coating 630, of less than 10 μm .

[0046] The hydrogenated silicon layers 611 are composed of the improved hydrogenated silicon material tuned to have a refractive index of greater than 3 and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1100 nm. Preferably, the hydrogenated silicon material has a refractive index of greater than 3.5 over the wavelength range of 800 nm to 1100 nm, *e.g.*, a refractive index of greater than 3.64, *i.e.*, about 3.6, at a wavelength of 830 nm. A higher refractive index is usually desirable. However, generally, the hydrogenated silicon material has a refractive index of less than 4.5 over the wavelength range of 800 nm to 1100 nm.

[0047] Preferably, the hydrogenated silicon material has an extinction coefficient of less than 0.0004 over the wavelength range of 800 nm to 1100 nm, more preferably, an extinction coefficient of less than 0.0003 over the wavelength range of 800 nm to 1100 nm. Typically, the hydrogenated silicon material has an extinction coefficient of greater than 0.01 at wavelengths of less than 600 nm, preferably, an extinction coefficient of greater than 0.05 at wavelengths of less than 650 nm. Because the hydrogenated silicon material is relatively strongly absorbing at wavelengths of less than 600 nm, an additional blocking stack is not necessary in the optical filter 600.

[0048] The lower-refractive-index layers 612 are composed of a lower-refractive-index material having a refractive index lower than that of the hydrogenated silicon layers 611 over the wavelength range of 800 nm to 1100 nm. Typically, the lower-refractive-index material has a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm. Preferably, the lower-refractive-index material has a refractive index of less than 2.5 over the wavelength range of 800 nm to 1100 nm, more preferably, a refractive index of less than 2 over the wavelength range of 800 nm to 1100 nm.

[0049] A lower refractive index is usually desirable for the lower-refractive-index layers 612 to increase the width of the blocking wavelength range, *i.e.*, the stopband, of the optical filter 600, allowing the same blocking level to be achieved with fewer layers in the filter stack 610. However, in some instances, a somewhat higher refractive index that is still lower than that of hydrogenated silicon layers 611 may be desirable to reduce the center-wavelength shift with change in incidence angle, *i.e.*, angle shift, of the optical filter 600.

[0050] In most instances, the lower-refractive-index material is a dielectric material, typically, an oxide. Suitable lower-refractive-index materials include silicon dioxide (SiO_2), aluminum oxide (Al_2O_3), titanium dioxide (TiO_2), niobium pentoxide (Nb_2O_5), tantalum pentoxide (Ta_2O_5), and mixtures thereof, *i.e.*, mixed oxides.

[0051] The optical filter 600 may be fabricated by using a sputtering process. Typically, the substrate 620 is provided in the vacuum chamber of a sputter-deposition system similar to that illustrated in FIG. 4. The hydrogenated silicon layers 611 and the lower-refractive-index layers 612 are then sequentially deposited on the first surface of the substrate 620 to form the filter stack 610 as a multilayer coating. Typically, the hydrogenated silicon layers 611 are deposited by pulsed-DC sputtering of a silicon target in the presence of hydrogen, as described heretofore. Also typically, the lower-refractive-index layers 612 are deposited by pulsed-DC sputtering of one or more suitable metal targets, *e.g.*, a silicon target, an aluminum target, a titanium target, a niobium target, and/or a tantalum target, in the presence of oxygen. The AR coating 630 is deposited on the second surface of the substrate 620 in a similar fashion. It should be noted that the order of forming the filter stack 610 and the AR coating 630 is usually unimportant.

[0052] The optical filter 600 is an interference filter having a passband at least partially overlapping with the wavelength range of 800 nm to 1100 nm. The passband may include the entire wavelength range of 800 nm to 1100 nm or, more typically, only a part of the wavelength range. The passband may be restricted to part or all of the wavelength range of 800 nm to 1100 nm, or may extend beyond the wavelength range. Preferably, the optical filter 600 has a transmittance level, within the passband, of greater than 90 % over the wavelength range of 800 nm to 1100 nm.

[0053] The optical filter 600 provides blocking outside of the passband, *i.e.*, a stopband on one or both sides of the passband, typically, over a wavelength range of 400 nm to 1100 nm, preferably, over a wavelength range of 300 nm to 1100 nm. Preferably, the optical filter 600 has a blocking level, outside of the passband, of greater than OD2 over the wavelength range of 400 nm to 1100 nm, more preferably, a blocking level of greater than OD3 over the wavelength range of 300 nm to 1100 nm.

[0054] In some instances, the optical filter 600 is a long-wavelength-pass edge filter, and the passband has an edge wavelength in the wavelength range of 800 nm to 1100 nm. However, in most instances, the optical filter 600 is a bandpass filter, preferably, a narrow bandpass filter. Typically, the passband has a center wavelength in the wavelength range of 800 nm to 1100 nm. Preferably, the passband has a full width at half maximum (FWHM) of less than 50 nm. Often, the entire passband is within the wavelength range of 800 nm to 1100 nm.

[0055] Generally, the optical filter 600 has a low center-wavelength shift with change in incidence angle. Preferably, the center wavelength of the passband shifts by less than 20 nm in magnitude with a change in incidence angle from 0° to 30°. Accordingly, the optical filter 600 has a wide incidence-angle acceptance range.

[0056] The optical filter 600 may have a variety of optical designs. In general, the optical design of the optical filter 600 is optimized for a particular passband by selecting suitable layer numbers, materials, and/or thicknesses for the filter stack 610. Some exemplary optical filters, described hereafter, include an Si:H/SiO₂ filter stack and a Ta₂O₅/SiO₂ AR coating, coated on opposite surfaces of a borofloat glass substrate.

[0057] With reference to FIG. 7, a first exemplary optical filter is a narrow bandpass filter that is designed to transmit light in a wavelength range of 829 nm to 859 nm over an incidence angle range of 0° to 30°. The first exemplary optical filter of FIG. 7 is comparable to the first conventional optical filter of FIG. 1, and some properties of the optical filters are compared in FIG. 7A. Design data, *i.e.*, layer numbers (from substrate to air), materials, and thicknesses, for the AR coating and the filter stack of the first exemplary filter are listed in FIGS. 7B and 7C, respectively. The filter stack includes 48 layers, the AR coating includes 5 layers, and the total coating thickness is about 5.7 μm.

[0058] Transmission spectra 700 and 701 at incidence angles of 0° and 30°, respectively, for the first exemplary optical filter are plotted in FIG. 7D. The first exemplary optical filter has a transmittance level, within the passband, of greater than 90%, and a blocking level, outside of the passband, of greater than OD3 over a wavelength range of 450 nm to 1050 nm. The passband has a center wavelength of about 850 nm and a FWHM of about 46.5 nm at an incidence angle of

0°. With change in incidence angle from 0° to 30°, the center wavelength of the passband shifts by about -12.2 nm.

[0059] Advantageously, the first exemplary optical filter of FIG. 7 includes fewer layers and has a smaller total coating thickness than the first conventional optical filter of FIG. 1. In particular, the total coating thickness of the first exemplary optical filter is about one quarter of the total coating thickness of the first conventional optical filter. Therefore, the first exemplary optical filter is less expensive to fabricate and is easier to pattern. Also advantageously, the first exemplary optical filter has a lower center-wavelength shift with change in incidence angle. Therefore, the passband of the first exemplary optical filter can be significantly narrower while accepting light over the same incidence angle range, improving the signal-to-noise ratio of systems incorporating the first exemplary optical filter.

[0060] The first exemplary optical filter may also be compared to an analogous optical filter including an Si/SiO₂ filter stack, *i.e.*, a filter stack including non-hydrogenated silicon layers, instead of an Si:H/SiO₂ filter stack. Transmission spectra 710 and 711 at incidence angles of 0° and 30°, respectively, for this optical filter are plotted in FIG. 7E. The transmittance level within the passband of this optical filter is too low to be useful.

[0061] With reference to FIG. 8, a second exemplary optical filter is a narrower bandpass filter that is designed to transmit light at a wavelength of 825 nm over an incidence angle range of 0° to 20°. The second exemplary optical filter of FIG. 8 is comparable to the second conventional optical filter of FIG. 2, and some properties of the optical filters are compared in FIG. 8A. Design data for the AR coating of the second exemplary optical filter, which is the same as that of the first exemplary optical filter, are listed in FIG. 7B. Design data for the filter stack of the second exemplary optical filter are listed in FIG. 8B. The filter stack includes 25 layers, the AR coating includes 5 layers, and the total coating thickness is about 3.3 μm.

[0062] Transmission spectra 800 and 801 at incidence angles of 0° and 20°, respectively, for the second exemplary optical filter are plotted in FIG. 8C. The second exemplary optical filter has a transmittance level, within the passband, of greater than 90%, and a blocking level, outside of the passband, of greater than OD2 over a wavelength range of 400 nm to 1100 nm. The passband has a center wavelength of about 829 nm and a FWHM of about 29.6 nm at an

incidence angle of 0° . With change in incidence angle from 0° to 20° , the center wavelength of the passband shifts by about -7.8 nm.

[0063] Similarly to the first exemplary optical filter of FIG. 7, the second exemplary optical filter of FIG. 8, advantageously, includes fewer layers, has a smaller total coating thickness, and has a lower center-wavelength shift with change in incidence angle than the second conventional optical filter of FIG. 2.

[0064] The second exemplary optical filter may also be compared to an analogous optical filter including an Si/SiO₂ filter stack instead of an Si:H/SiO₂ filter stack. Transmission spectra 810 and 811 at incidence angles of 0° and 20° , respectively, for this optical filter are plotted in FIG. 8D. The transmittance level within the passband of this optical filter is too low to be useful.

[0065] With reference to FIG. 9, a third exemplary optical filter is a narrow bandpass filter that is designed to transmit light over a wavelength range of 845 nm to 865 nm over an incidence angle range of 0° to 40° . The third exemplary optical filter of FIG. 9 is comparable to the third conventional optical filter of FIG. 3. Design data for the AR coating of the third exemplary optical filter, which is the same as that of the first exemplary optical filter, are listed in FIG. 7B. Design data for the filter stack of the third exemplary optical filter are listed in FIG. 9A. The filter stack includes 29 layers, the AR coating includes 5 layers, and the total coating thickness is about $4.8\text{ }\mu\text{m}$.

[0066] Transmission spectra 900 and 901 at incidence angles of 0° and 40° , respectively, for the third exemplary optical filter are plotted in FIG. 9B. The third exemplary optical filter of FIG. 9 has substantially the same passband width as the third conventional optical filter of FIG. 3, but has a slightly lower transmittance level within the passband. Advantageously, however, the third exemplary optical filter accepts light over a considerably larger incidence angle range of 0° to 40° than the third conventional optical filter, which accepts light over an incidence angle range of only 0° to 24° . In other words, the third exemplary optical filter has a significantly wider incidence-angle acceptance range. Also advantageously, the third exemplary optical filter includes fewer layers and has a smaller total coating thickness, about one fifth of the total coating thickness of the third conventional optical filter.

[0067] As mentioned heretofore, the optical filter of the present invention is particularly useful when it forms part of a sensor system, such as a proximity sensor system, a 3D imaging system, or a gesture-recognition system. With reference to FIG. 10, a typical sensor system 1000 includes a light source 1010, an optical filter 1020 according to the present invention, and a sensor 1030. Note that other elements commonly included in a sensor system, such as optics, are omitted for simplicity of illustration.

[0068] The light source 1010 emits light at an emission wavelength in a wavelength range of 800 nm to 1100 nm. Typically, the light source 1010 emits modulated light, *e.g.*, light pulses. Preferably, the light source 1010 is a light-emitting diode (LED), an LED array, a laser diode, or a laser diode array. The light source 1010 emits light towards a target 1040, which reflects the emitted light back towards the sensor system 1000. When the sensor system 1000 is a gesture-recognition system, the target 1040 is a user of the gesture-recognition system.

[0069] The optical filter 1020 is disposed to receive the emitted light after reflection by the target 1040. The optical filter 1020 has a passband including the emission wavelength and at least partially overlapping with the wavelength range of 800 nm to 1100 nm. Typically, the optical filter 1020 is a bandpass filter, preferably, a narrow bandpass filter, as described heretofore. The optical filter 1020 transmits the emitted light from the light source 1010, while substantially blocking ambient light. In short, the optical filter 1020 receives the emitted light from the light source 1010, after reflection by the target 1040, and transmits the emitted light to the sensor 1030.

[0070] The sensor 1030 is disposed to receive the emitted light after transmission by the optical filter 1020, *i.e.*, the sensor 1030 is disposed behind the optical filter 1020. In some instances, the optical filter 1020 is formed directly on the sensor 1030 and, thus, disposed on the sensor 1030. For example, the optical filter 1020 may be coated and patterned, *e.g.*, by photolithography, on sensors, *e.g.*, proximity sensors, in wafer level processing (WLP).

[0071] When the sensor system 1000 is a proximity sensor system, the sensor 1030 is a proximity sensor, which detects the emitted light to sense a proximity of the target 1040, according to methods known in the art. When the sensor system 1000 is a 3D-imaging system or a gesture-recognition system, the sensor 1030 is a 3D image sensor, *e.g.*, a charge-coupled

device (CCD) chip or a complementary metal oxide semiconductor (CMOS) chip, which detects the emitted light to provide a 3D image of the target 1040, which, in some instances, is the user. Typically, the 3D image sensor converts the optical information into an electrical signal for processing by a processing system, *e.g.*, an application-specific integrated circuit (ASIC) chip or a digital signal processor (DSP) chip, according to methods known in the art. For example, when the sensor system 1000 is a gesture-recognition system, the processing system processes the 3D image of the user to recognize a gesture of the user.

WE CLAIM:

1. An optical filter, comprising:
a filter stack comprising:
a plurality of thin film hydrogenated silicon layers, wherein the plurality of thin film hydrogenated silicon layers have a refractive index of greater than 3 over a wavelength range of 800 nm to 1100 nm; and
a plurality of thin film dielectric lower-refractive-index layers, wherein the plurality of thin film dielectric lower-refractive-index layers have a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm, and wherein the plurality of thin film dielectric lower-refractive-index layers alternate, in a one-to-one ratio, with the plurality of thin film hydrogenated silicon layers; and
wherein the optical filter has exhibits interference that creates a passband at least partially overlapping with the wavelength range of 800 nm to 1100 nm,
wherein the passband has a center wavelength that shifts by less than 20 nm in magnitude with a change in an incidence angle between 0° to 30°.
2. The optical filter of claim 1, wherein the plurality of thin film hydrogenated silicon layers each have a refractive index of greater than 3.6 at a wavelength of 830 nm.
3. The optical filter of claim 1, wherein the plurality of thin film hydrogenated silicon layers each have a refractive index of greater than 3.5 over the wavelength range of 800 nm to 1100 nm.
4. The optical filter of claim 1, wherein the plurality of thin film hydrogenated silicon layers each have a refractive index of greater than 3.6 over the wavelength range of 800 nm to 1100 nm.
5. The optical filter of claim 1, wherein the plurality of thin film dielectric lower-refractive-index layers each have a refractive index of less than 2.5 over the wavelength range of 800 nm to 1100 nm.
6. The optical filter of claim 1, wherein the plurality of thin film dielectric lower-refractive-index layers each have a refractive index of less than 2 over the wavelength range of 800 nm to 1100 nm.

7. The optical filter of claim 1, wherein the passband has a center wavelength that shifts by less than 15 nm in magnitude with a change in the incidence angle between 0° to 30°.
8. The optical filter of claim 1, wherein the passband has a center wavelength that shifts by about 12.2 nm in magnitude with a change in the incidence angle between 0° to 30°.
9. The optical filter of claim 1, wherein the plurality of thin film dielectric lower-refractive-index layers are each composed of silicon dioxide (SiO₂), aluminum oxide (Al₂O₃), titanium dioxide (TiO₂), niobium pentoxide (Nb₂O₅), tantalum pentoxide (Ta₂O₅), or a mixture thereof.
10. The optical filter of claim 1, wherein the optical filter has a transmittance level, within the passband, of greater than 90% over the wavelength range of 800 nm to 1100 nm.
11. The optical filter of claim 1, wherein the optical filter has a blocking level, outside of the passband, of greater than OD2 over a wavelength range of 400 nm to 1100 nm.
12. The optical filter of claim 1, wherein the optical filter is a long-wavelength-pass edge filter, and wherein the passband has an edge wavelength in the wavelength range of 800 nm to 1100 nm.
13. The optical filter of claim 1, wherein the optical filter is a bandpass filter, and wherein the passband has a center wavelength in the wavelength range of 800 nm to 1100 nm.
14. The optical filter of claim 1, wherein the passband has a full width at half maximum (FWHM) of less than 50 nm.
15. The optical filter of claim 1, further comprising:
a substrate, wherein the filter stack is disposed on a first surface of the substrate and a coating is disposed on a second surface of the substrate opposite the first surface.
16. The optical filter of claim 15, wherein the coating is an antireflective (AR) coating.
17. The optical filter of claim 1, wherein the optical filter has a total coating thickness of less than 10 μm.

18. The optical filter of claim 1, forming part of a sensor system including a light source for emitting light at an emission wavelength within the passband of the optical filter, and a sensor for detecting the emitted light,

wherein the optical filter receives the emitted light from the light source and transmits the emitted light to the sensor.

19. The optical filter of claim 1, wherein the plurality of thin film hydrogenated silicon layers are each deposited by pulsed direct current (DC) sputtering.

20. The optical filter of claim 1, wherein the plurality of thin film hydrogenated silicon layers are associated with an extinction coefficient of approximately 0.00055 at 800 nm.

21. The optical filter of claim 1, wherein the plurality of thin film hydrogenated silicon layers are associated with an extinction coefficient of less than 0.0003 at 800 nm.

22. A sensor system, comprising:

an optical filter, exhibiting interference that creates a passband including an emission wavelength and at least partially overlapping with a wavelength range of 800 nm to 1100 nm, being disposed to receive emitted light and transmit the emitted light,

wherein the emitted light is emitted, from a light source, at the emission wavelength in the wavelength range of 800 nm to 1100 nm, and

wherein the optical filter includes a filter stack including:

a plurality of thin film hydrogenated silicon layers,

wherein the plurality of thin film hydrogenated silicon layers each have a refractive index of greater than 3 over the wavelength range of 800 nm to 1100 nm; and

a plurality of thin film dielectric lower-refractive-index layers,

wherein the plurality of thin film dielectric lower-refractive-index layers each have a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm, and

wherein thin film dielectric lower-refractive-index layers, of the plurality of thin film dielectric lower-refractive-index layers, alternate, in a one-to-one ration, with thin film hydrogenated silicon layers of the plurality of thin film hydrogenated silicon layers,

wherein the passband has a center wavelength that shifts by less than 20 nm in magnitude with a change in an incidence angle between 0° to 30°.

23. The sensor system of claim 22, wherein the optical filter is disposed directly on a sensor.

24. The sensor system of claim 22, further comprising:

a sensor, wherein the sensor system is a proximity sensor system, the emitted light is directed toward a target, the optical filter is disposed to receive the emitted light after reflection by the target, and the sensor is a proximity sensor for detecting the emitted light and sensing a proximity of the target.

25. The sensor system of claim 22, further comprising:

a sensor, wherein the sensor system is a three-dimensional (3D) imaging system, the emitted light is directed toward a target, the optical filter is disposed to receive the emitted light after reflection by the target, and the sensor is a 3D image sensor for detecting the emitted light and providing a 3D image of the target.

26. The sensor system of claim 25, wherein the 3D imaging system is a gesture-recognition system, the target is a user of the gesture-recognition system, and the sensor system further includes:

a processing system for processing a 3D image of the user to recognize a gesture of the user.

27. The sensor system of claim 22, further comprising: a sensor, wherein the sensor is a charge-coupled device (CCD) chip or a complementary metal oxide semiconductor (CMOS) chip.

28. The sensor system of claim 22, further comprising: a sensor, wherein the optical filter is formed directly on the sensor by using wafer-level processing.

29. The sensor system of claim 22, wherein the optical filter further includes:

a substrate, wherein the filter stack is disposed on a first surface of the substrate; and
an antireflective (AR) coating is disposed on a second surface of the substrate opposite the first surface.

30. A system, comprising:
 an optical filter, exhibits interference that creates a passband including an emission wavelength and at least partially overlapping with a wavelength range of 800 nm to 1100 nm;
 wherein the optical filter includes a filter stack including:
 a plurality of thin film hydrogenated silicon layers, wherein the plurality of thin film hydrogenated silicon layers have a refractive index of greater than 3.5 over a wavelength range of 800 nm to 1100 nm; and
 a plurality of thin film dielectric lower-refractive-index layers, wherein the plurality of thin film dielectric lower-refractive-index layers have a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm, and wherein thin film dielectric lower-refractive-index layers, of the plurality of thin film dielectric lower-refractive-index layers, alternate, in a one-to-one ratio, with thin film hydrogenated silicon layers of the plurality of thin film hydrogenated silicon layers, and
 wherein the passband has a center wavelength that shifts by less than 20 nm in magnitude with a change in an incidence angle between 0° to 30°.
31. The system of claim 30, wherein the passband has a full width at half maximum of less than 50 nm.
32. The system of claim 30, further comprising: a substrate, wherein the filter stack is disposed on a first surface of the substrate and a coating is disposed on a second surface of the substrate opposite the first surface.
33. A method, comprising:
 forming, using a direct current (DC) sputtering technique, a plurality of hydrogenated silicon layers of an optical filter,
 the plurality of hydrogenated silicon layers having a first refractive index of greater than 3 over an operating wavelength range of the optical filter of 800 nanometers (nm) to 1100 nm, and
 the plurality of hydrogenated silicon layers being formed in a deposition chamber associated with a chamber pressure of less than 2 millitorr (mTorr); and
 forming a plurality of lower-refractive-index layers of the optical filter,

the plurality of lower-refractive-index layers each having a second refractive index of less than 3 over the operating wavelength range of the optical filter of 800 nm to 1100 nm, and

the plurality of lower-refractive-index layers being stacked in alternation with the plurality of hydrogenated silicon layers.

34. The method of claim 33, where the DC sputtering technique is a magnetron DC sputtering technique.

35. The method of claim 33, where the DC sputtering technique is a pulsed DC sputtering technique.

36. The method of claim 33, where forming the plurality of hydrogenated silicon layers comprises:

sputtering silicon to deposit the plurality of hydrogenated silicon layers onto a substrate.

37. The method of claim 36, where sputtering the silicon comprises:
sputtering the silicon using a circular cathode with a silicon target.

38. The method of claim 37, where a first diameter of the circular cathode is between one times (1x) a second diameter of the substrate and two times (2x) the second diameter of the substrate.

39. The method of claim 37, where a throw distance between a first plane of the substrate and a second plane of the silicon target is between one half times (0.5x) a diameter of the substrate and two times (2x) the diameter of the substrate.

40. The method of claim 36, where the substrate is transparent in the operating wavelength range.

41. The method of claim 33, where the plurality of hydrogenated silicon layers are associated with an extinction coefficient of approximately 0.00055 at 800 nm.

42. The method of claim 33, where the plurality of hydrogenated silicon layers are associated with an extinction coefficient of less than 0.0003 at 800 nm.

43. The method of claim 33, where the plurality of hydrogenated silicon layers and the plurality of lower-refractive-index layers are a multilayer structure; and
the method further comprises:
annealing the multilayer structure at a temperature of between 250 degrees Celsius and 350 degrees Celsius.
44. The method of claim 33, where the plurality of hydrogenated silicon layers and the plurality of lower-refractive-index layers are a multilayer structure; and
the method further comprises:
annealing the multilayer structure for a period of between 30 minutes and 90 minutes.
45. The method of claim 33, further comprising:
providing hydrogen plasma into the deposition chamber using a plasma activation source.
46. The method of claim 33, where the plurality of hydrogenated silicon layers and the plurality of lower-refractive-index layers are a multilayer structure; and
the method further comprises:
forming the multilayer structure on a semiconductor sensor chip using a wafer-level processing technique.
47. The method of claim 46, where the semiconductor sensor chip includes at least one of:
a charge-coupled device (CCD) chip, or
a complementary metal oxide semiconductor (CMOS) chip.
48. The method of claim 33, where forming the plurality of hydrogenated silicon layers comprises:
forming the plurality of hydrogenated silicon layers at a deposition rate of between 0.05 nanometers per second (nm/s) and 1.2 nm/s.
49. The method of claim 33, where forming the plurality of hydrogenated silicon layers comprises:

forming the plurality of hydrogenated silicon layers at a deposition rate of 0.6 nanometers per second to 1.0 nanometers per second.

50. A method of fabricating an optical filter, comprising:

fabricating a plurality of hydrogenated silicon (Si:H) layers of a multilayer structure of the optical filter using a direct current (DC) sputtering technique,

the plurality of Si:H layers being fabricated in a low-pressure deposition chamber associated with a chamber pressure of 2 millitorr (mTorr), and

the plurality of Si:H layers having a first refractive index of greater than 3 over an operating wavelength range of the optical filter of 800 nanometers (nm) to 1100 nm; and fabricating a plurality of lower-refractive-index (LI) layers,

the plurality of LI layers having a second refractive index of less than 3 over the operating wavelength range of the optical filter of 800 nm to 1100 nm, and

the plurality of LI layers being stacked in alternation with the plurality of Si:H layers.

51. The method of claim 50, further comprising:

annealing the multilayer structure of the optical filter at a temperature of between 250 degrees Celsius and 350 degrees Celsius.

52. The method of claim 50, where the plurality of Si:H layers are associated with an extinction coefficient of less than 0.0003 at 800 nm.

53. An optical filter comprising:

a filter stack comprising:

a plurality of hydrogenated silicon layers, wherein the plurality of hydrogenated silicon layers have a refractive index of greater than 3 over a wavelength range of 800 nm to 1100 nm and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1100 nm; and

a plurality of lower-refractive-index layers, wherein the plurality of lower-refractive-index layers each have a refractive index of less than 3 over the wavelength

range of 800 nm to 1100 nm, and wherein the plurality of lower-refractive-index layers are stacked in alternation with the plurality of hydrogenated silicon layers;

wherein the optical filter has a passband at least partially overlapping with the wavelength range of 800 nm to 1100 nm,

wherein the passband has a center wavelength that shifts by less than 20 nm in magnitude with a change in an incidence angle between 0° to 30° , thereby providing the optical filter with a wide incidence-angle acceptance range.

54. The optical filter of claim 53, wherein the plurality of hydrogenated silicon layers each have a refractive index of greater than 3.6 at a wavelength of 830 nm.

55. The optical filter of claim 53, wherein the plurality of hydrogenated silicon layers each have a refractive index of greater than 3.5 over the wavelength range of 800 nm to 1100 nm.

56. The optical filter of claim 53, wherein the plurality of hydrogenated silicon layers each have an absorption coefficient of less than 0.0004 over the wavelength range of 800 nm to 1100 nm.

57. The optical filter of claim 53, wherein the plurality of lower-refractive-index layers each have a refractive index of less than 2.5 over the wavelength range of 800 nm to 1100 nm.

58. The optical filter of claim 53, wherein the plurality of lower-refractive-index layers are each composed of silicon dioxide (SiO_2), aluminum oxide (Al_2O_3), titanium dioxide (TiO_2), niobium pentoxide (Nb_2O_5), tantalum pentoxide (Ta_2O_5), or a mixture thereof.

59. The optical filter of claim 53, wherein the optical filter has a transmittance level, within the passband, of greater than 90% over the wavelength range of 800 nm to 1100 nm.

60. The optical filter of claim 53, wherein the optical filter has a blocking level, outside of the passband, of greater than OD2 over a wavelength range of 400 nm to 1100 nm.

61. The optical filter of claim 53, wherein the optical filter is a long-wavelength-pass edge filter, and wherein the passband has an edge wavelength in the wavelength range of 800 nm to 1100 nm.

62. The optical filter of claim 53, wherein the optical filter is a bandpass filter, and wherein the passband has a center wavelength in the wavelength range of 800 nm to 1100 nm.
63. The optical filter of claim 62, wherein the passband has a full width at half maximum (FWHM) of less than 50 nm.
64. The optical filter of claim 53, further comprising:
a substrate, wherein the filter stack is disposed on a first surface of the substrate; and
an antireflective (AR) coating disposed on a second surface of the substrate opposite the first surface.
65. The optical filter of claim 64, wherein the optical filter has a total coating thickness of less than 10 μm .
66. The optical filter of claim 53, forming part of a sensor system including a light source for emitting light at an emission wavelength within the passband of the optical filter, and a sensor for detecting the emitted light,
wherein the optical filter receives the emitted light from the light source and transmits the emitted light to the sensor.
67. The optical filter of claim 53, wherein the plurality of hydrogenated silicon layers are each deposited by pulsed direct current (DC) sputtering.
68. A sensor system comprising:
an optical filter, having a passband including an emission wavelength and at least partially overlapping with a wavelength range of 800 nm to 1100 nm, being disposed to receive emitted light and transmit the emitted light,
wherein the emitted light is, emitted from a light source, at the emission wavelength in the wavelength range of 800 nm to 1100 nm, and
wherein the optical filter includes a filter stack including:
a plurality of hydrogenated silicon layers, wherein the plurality of hydrogenated silicon layers each have a refractive index of greater than 3 over the

wavelength range of 800 nm to 1100 nm and an extinction coefficient of less than 0.0005 over the wavelength range of 800 nm to 1100 nm; and

a plurality of lower-refractive-index layers, wherein the plurality of lower-refractive-index layers each have a refractive index of less than 3 over the wavelength range of 800 nm to 1100 nm, and

wherein the plurality of lower-refractive-index layers are stacked in alternation with the plurality of hydrogenated silicon layers, wherein a passband of the optical filter has a center wavelength that shifts by less than 20 nm in magnitude with a change in an incidence angle between 0° to 30° , thereby providing the optical filter with a wide incidence-angle acceptance range; and

a sensor, disposed to receive the emitted light after transmission by the optical filter, for detecting the emitted light.

69. The sensor system of claim 68, wherein the optical filter is disposed directly on the sensor.

70. The sensor system of claim 68, wherein
the sensor system is a proximity sensor system,
the emitted light is directed toward a target,
the optical filter is disposed to receive the emitted light after reflection by the target, and
the sensor is a proximity sensor for detecting the emitted light and sensing a proximity of the target.

71. The sensor system of claim 68, wherein
the sensor system is a three-dimensional (3D) imaging system,
the emitted light is directed toward a target,
the optical filter is disposed to receive the emitted light after reflection by the target, and
the sensor is a 3D image sensor for detecting the emitted light and providing a 3D image of the target.

72. The sensor system of claim 71, wherein
the 3D imaging system is a gesture-recognition system,
the target is a user of the gesture-recognition system, and

the sensor system further includes: a processing system for processing the 3D image of the user to recognize a gesture of the user.

73. The sensor system of claim 68, wherein the sensor is a charge-coupled device (CCD) chip or a complementary metal oxide semiconductor (CMOS) chip.

74. The sensor system of claim 68, wherein the optical filter is formed directly on the sensor by using wafer-level processing.

75. The sensor system of claim 68, wherein the optical filter further includes:
a substrate, wherein the filter stack is disposed on a first surface of the substrate; and
an antireflective (AR) coating disposed on a second surface of the substrate opposite the first surface.

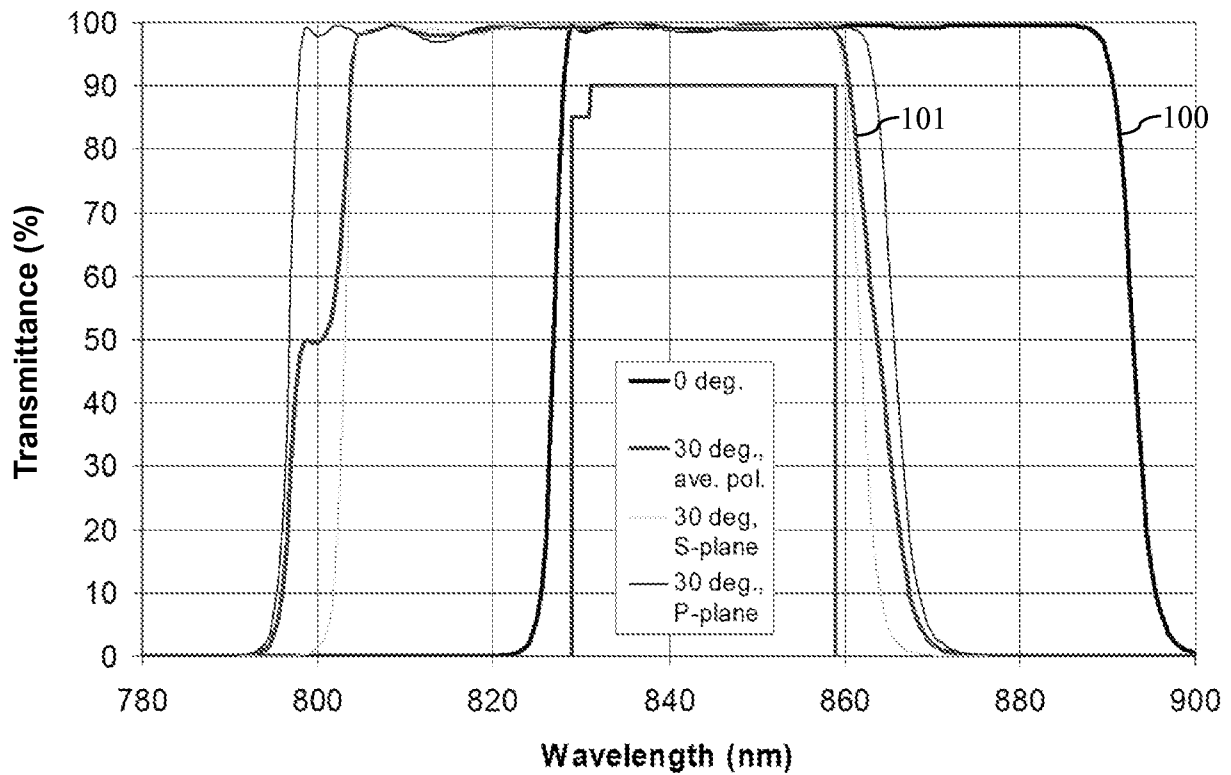


FIG. 1
PRIOR ART

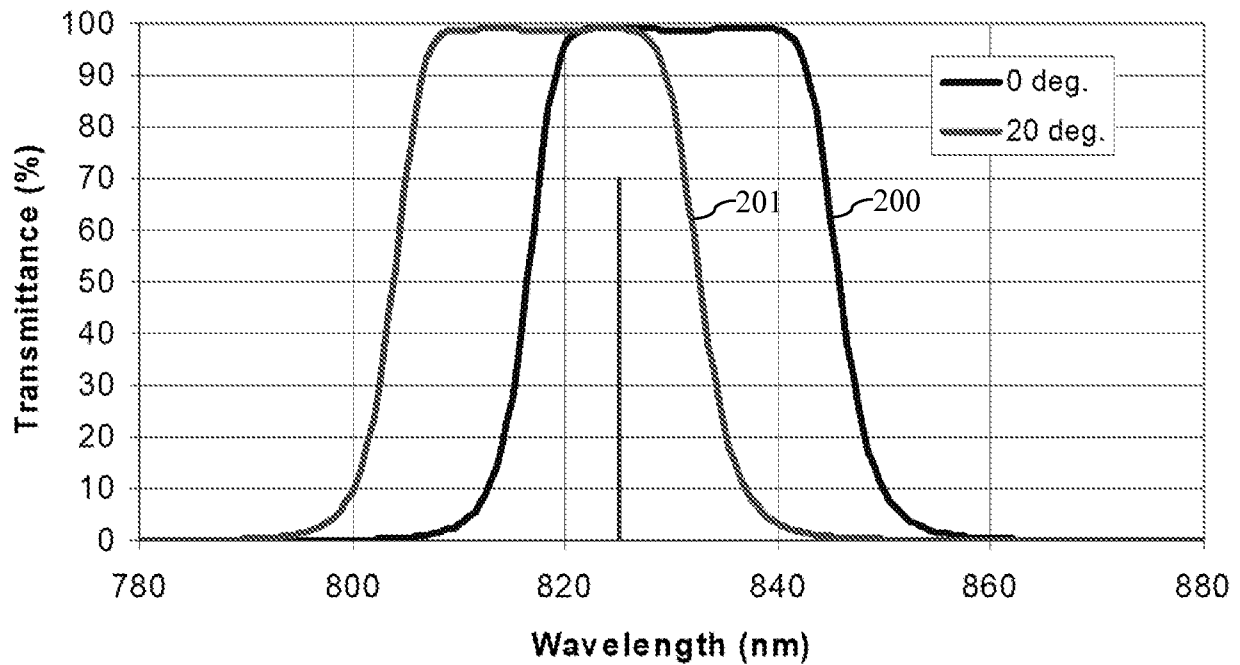


FIG. 2
PRIOR ART

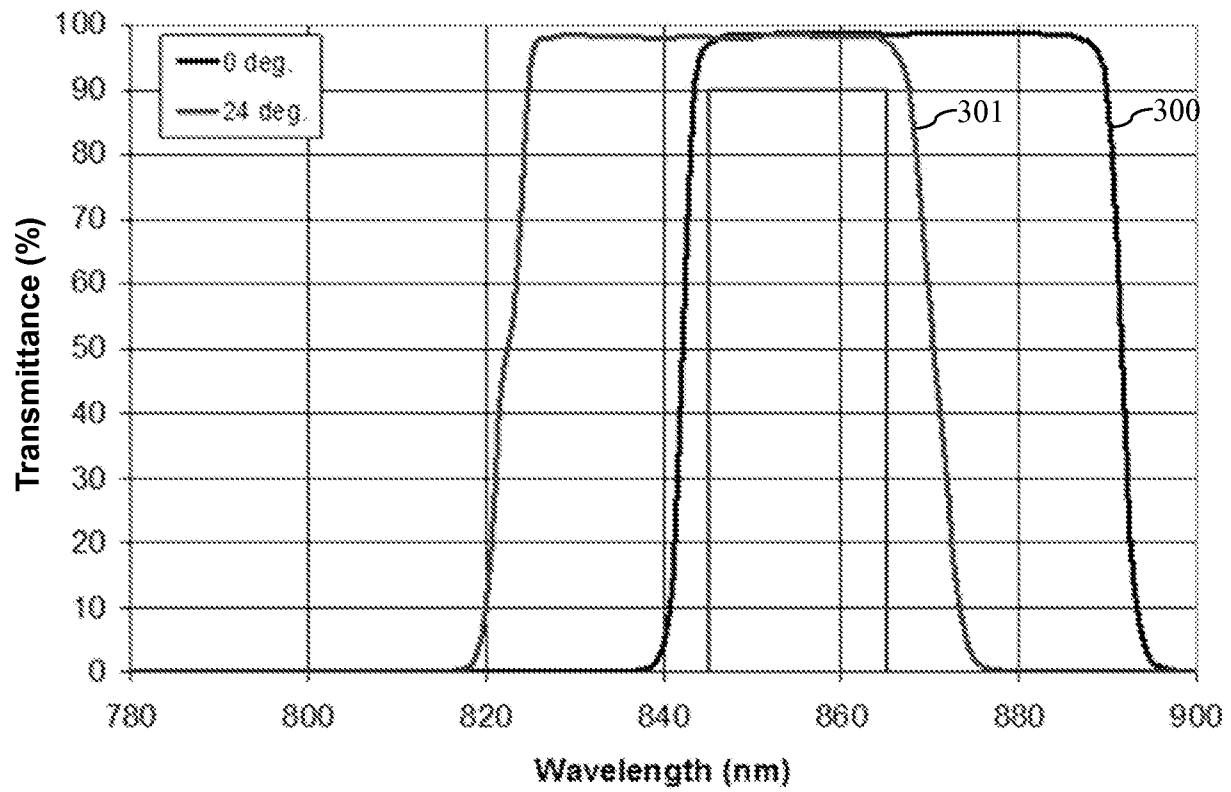


FIG. 3
PRIOR ART

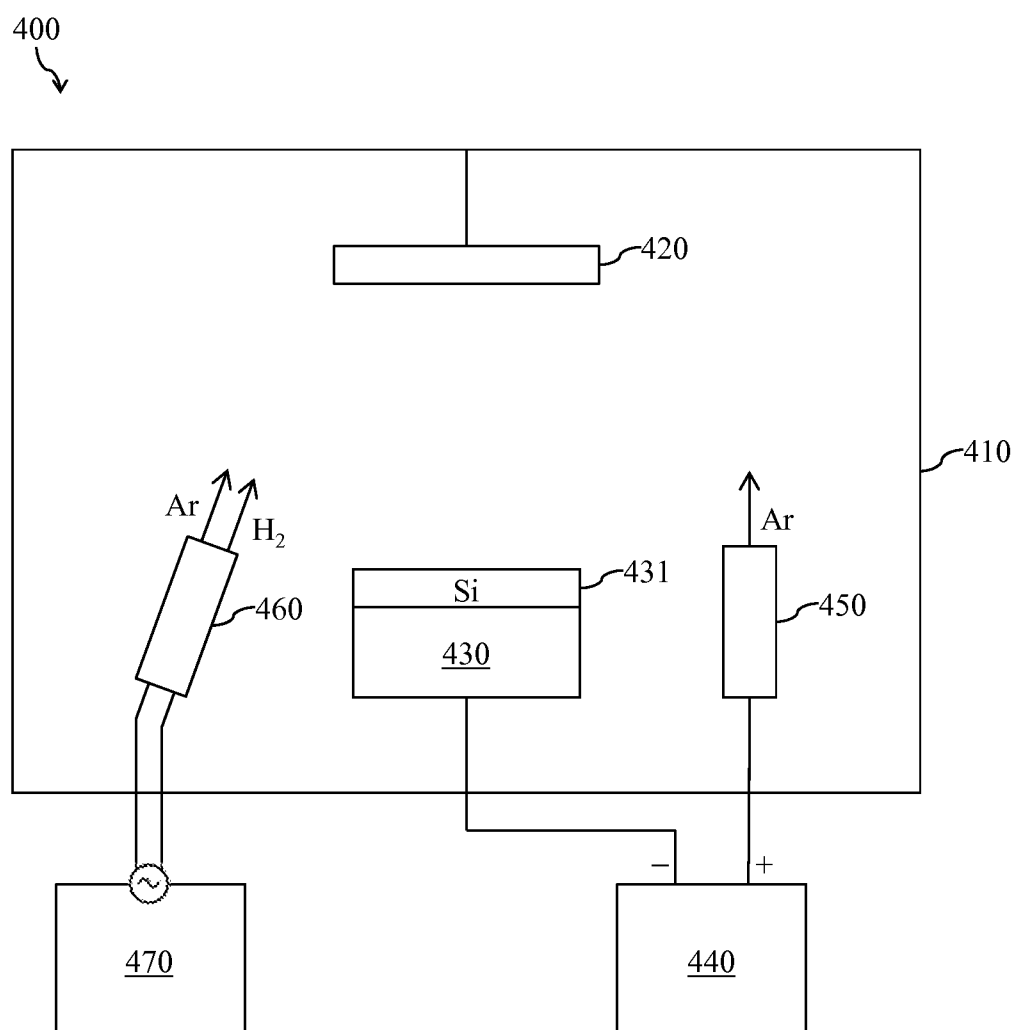
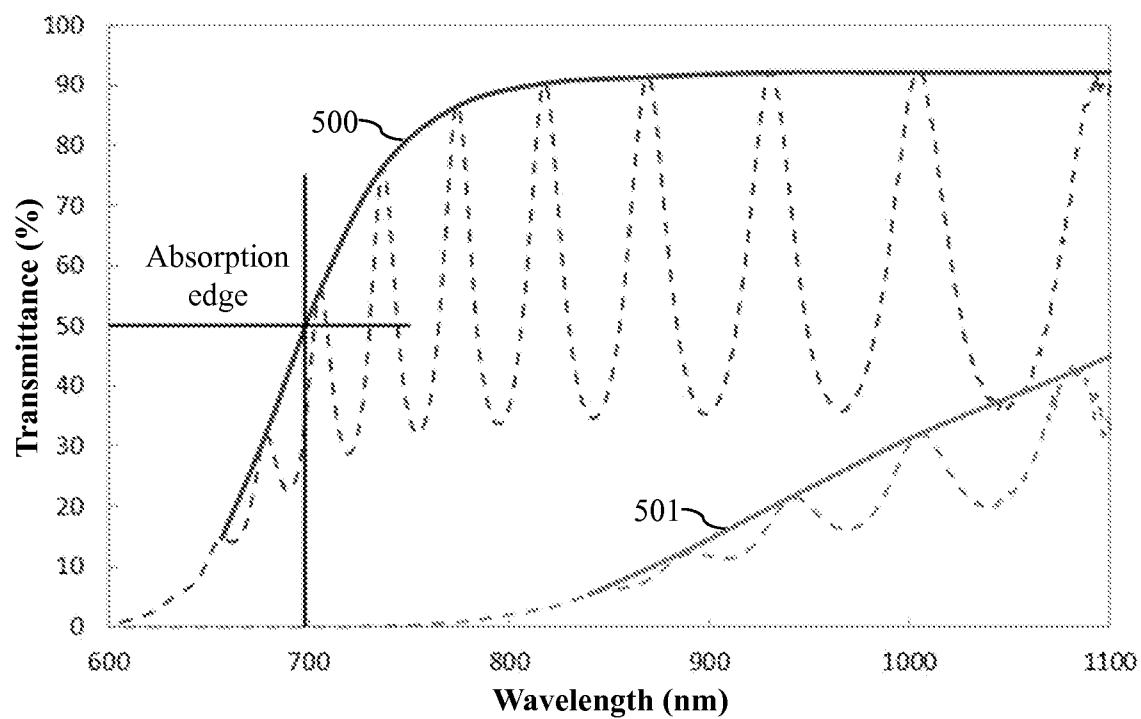
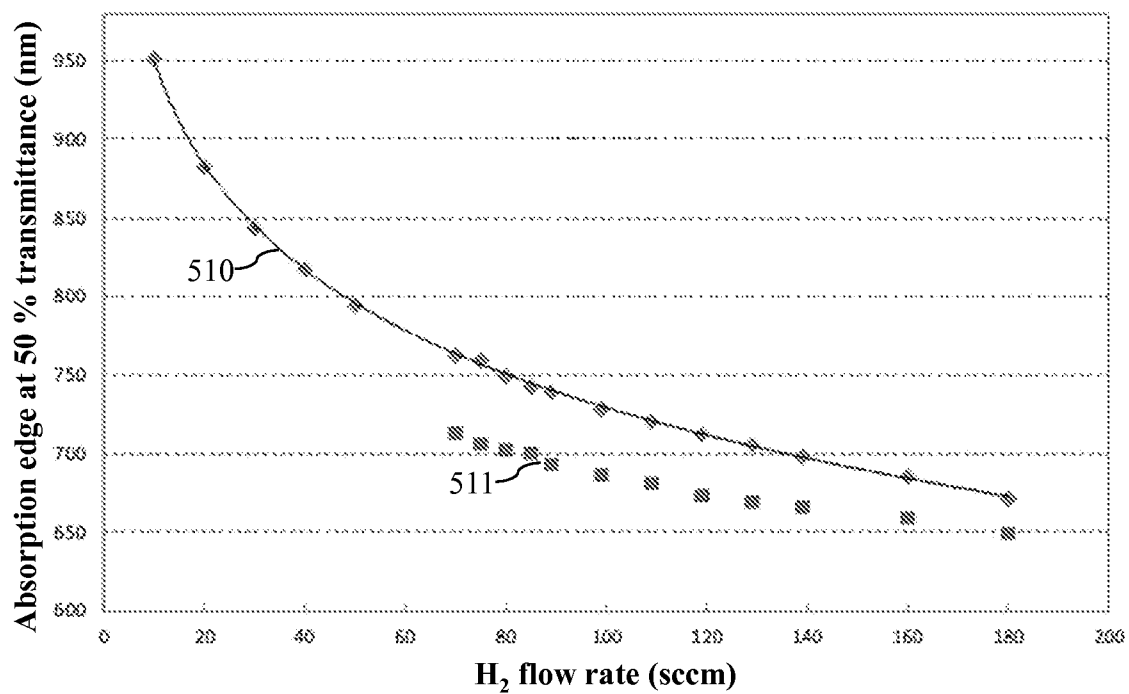


FIG. 4

**FIG. 5A****FIG. 5B**

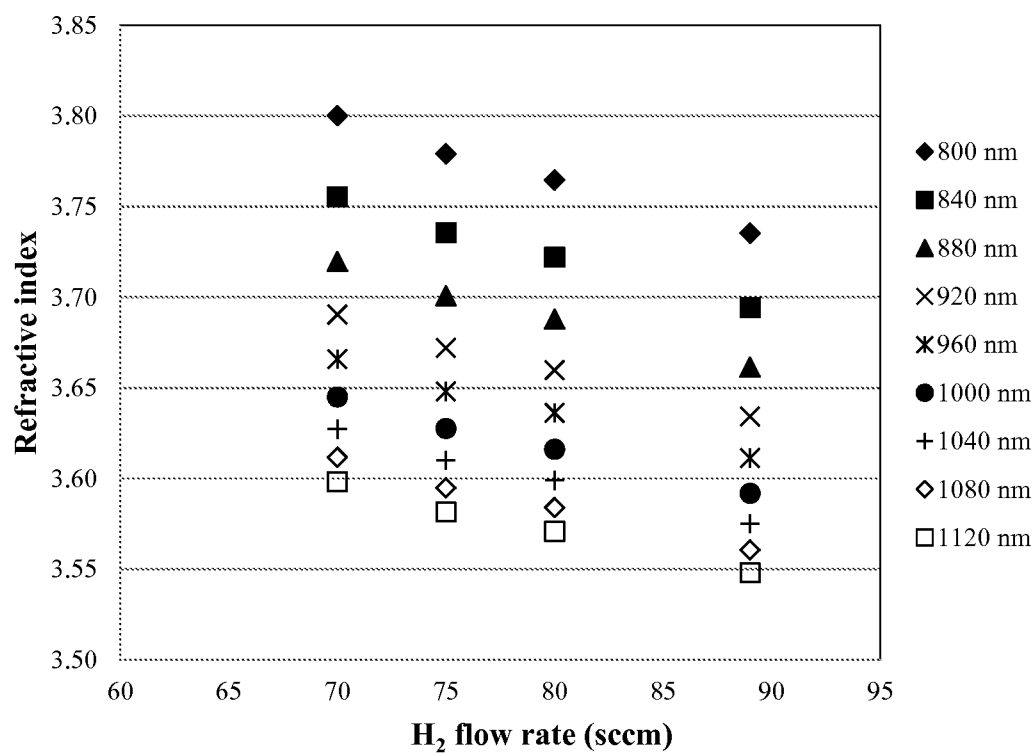


FIG. 5C

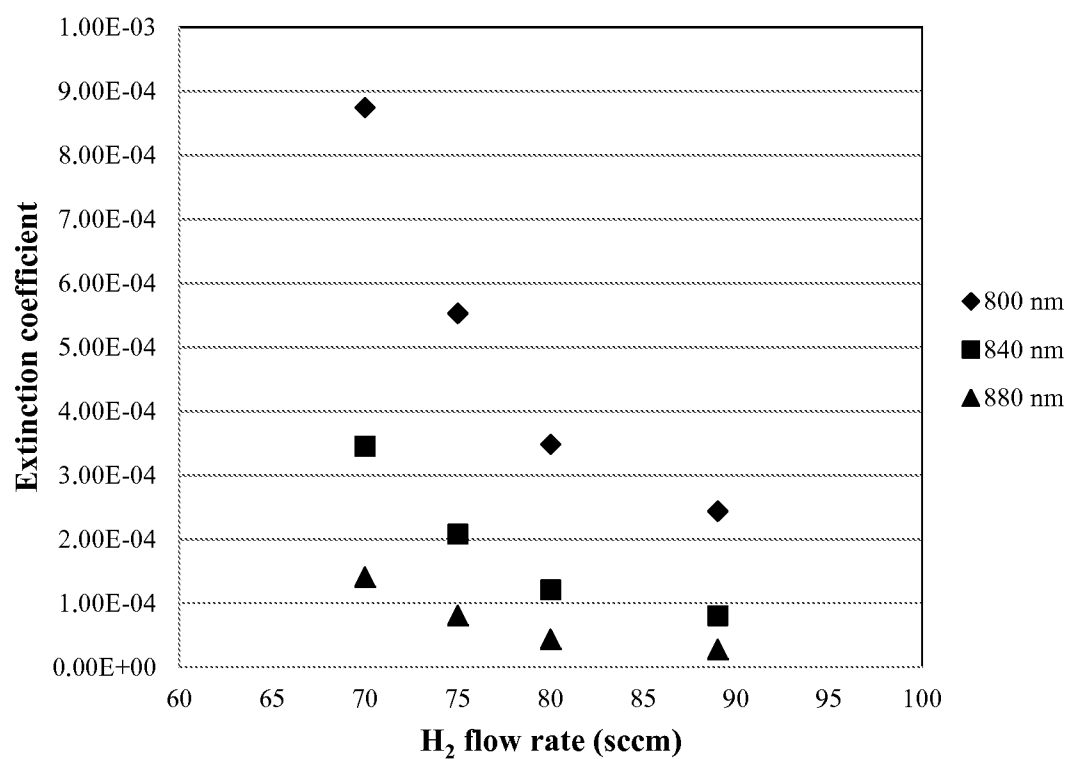
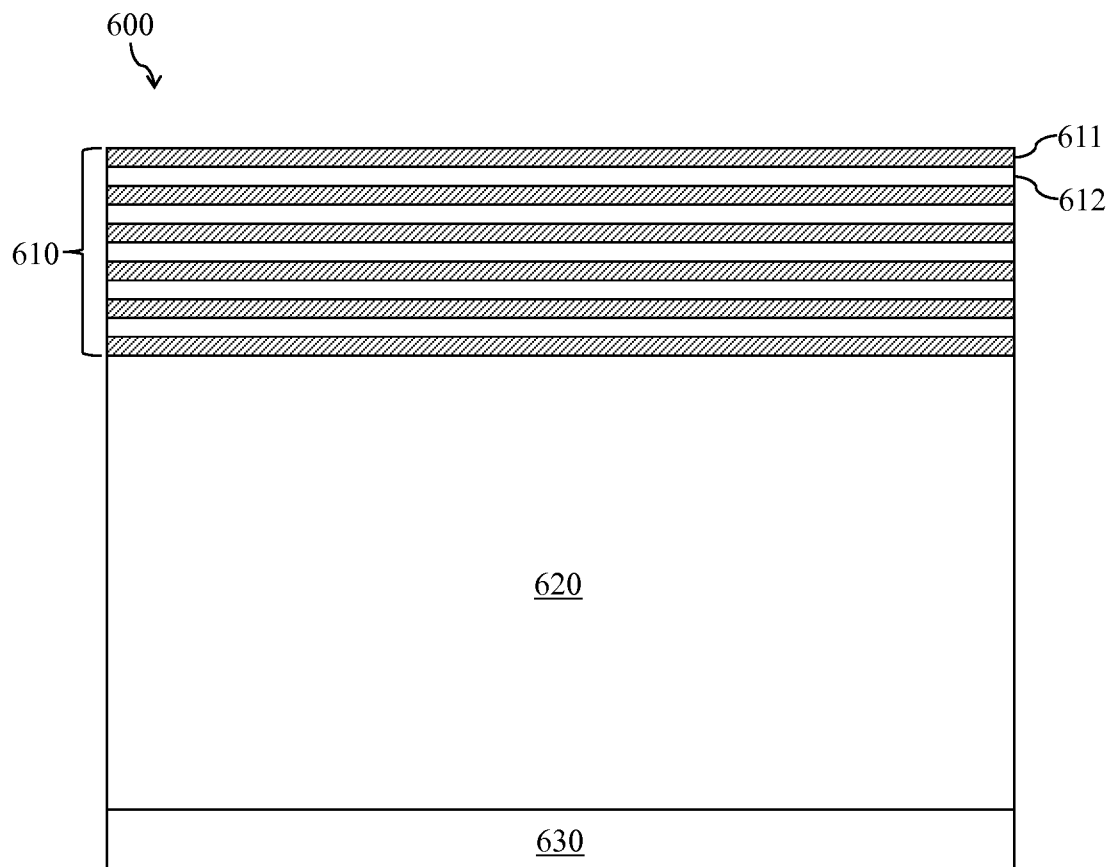


FIG. 5D

**FIG. 6**

Comparison of First Conventional Optical Filter and First Exemplary Optical Filter		
Property	First Conventional Optical Filter	First Exemplary Optical Filter
FWHM (nm)	66.0	46.5
Center-wavelength shift, 0° to 30° (nm)	-29.1	-12.2
Background transmittance for 2856 K blackbody (%)	14.8	9.75
Total coating thickness (nm)	24432	5688

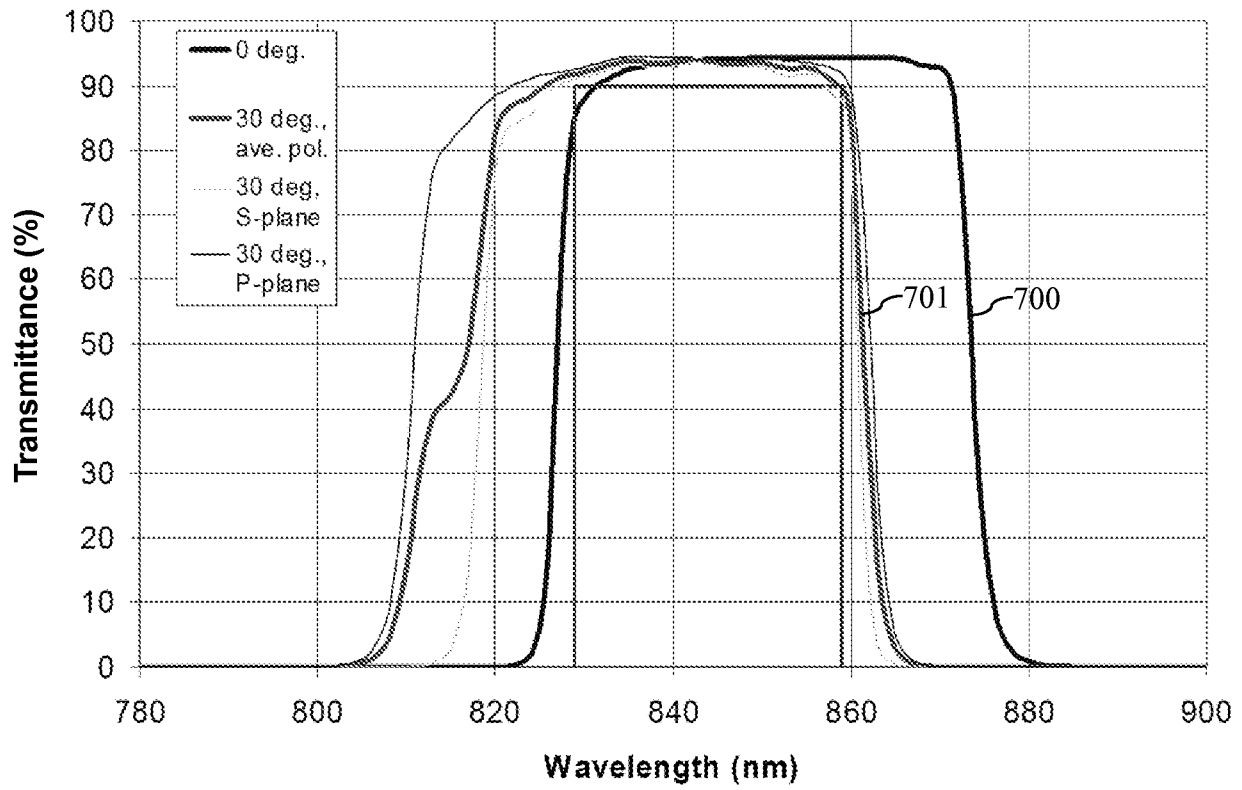
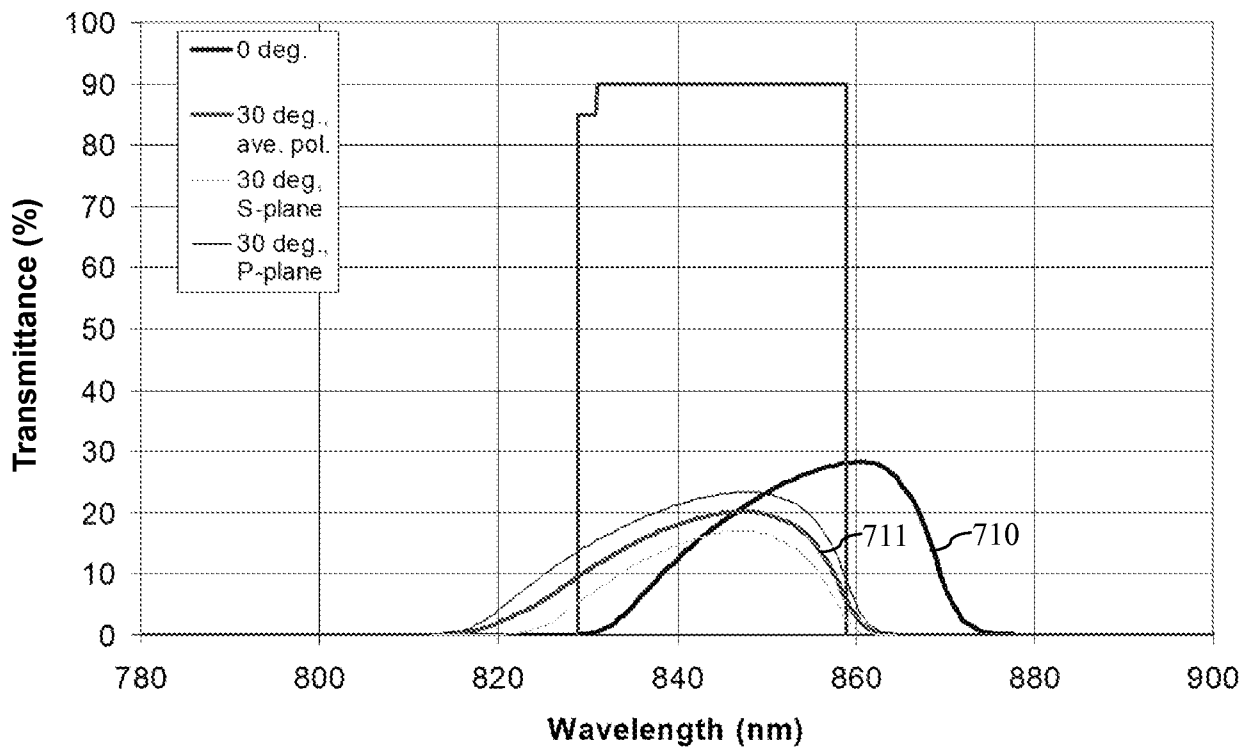
FIG. 7A

AR Coating of First Exemplary Optical Filter		
Layer No.	Material	Thickness (nm)
1	SiO ₂	153.5852
2	Ta ₂ O ₅	32.39649
3	SiO ₂	47.88567
4	Ta ₂ O ₅	112.6954
5	SiO ₂	146.4009

FIG. 7B

Filter Stack of First Exemplary Optical Filter					
Layer No.	Material	Thickness (nm)	Layer No.	Material	Thickness (nm)
1	Si:H	12.06225	25	Si:H	123.9279
2	SiO ₂	207.0239	26	SiO ₂	73.3697
3	Si:H	112.2893	27	Si:H	92.284
4	SiO ₂	131.3289	28	SiO ₂	93.71968
5	Si:H	58.57214	29	Si:H	57.99244
6	SiO ₂	123.472	30	SiO ₂	129.6102
7	Si:H	121.8488	31	Si:H	118.8611
8	SiO ₂	62.37868	32	SiO ₂	121.0311
9	Si:H	94.08999	33	Si:H	58.78395
10	SiO ₂	91.40882	34	SiO ₂	126.8949
11	Si:H	68.58871	35	Si:H	27.06202
12	SiO ₂	97.34483	36	SiO ₂	265.4308
13	Si:H	126.2579	37	Si:H	107.9248
14	SiO ₂	65.22393	38	SiO ₂	103.3531
15	Si:H	87.89165	39	Si:H	33.0597
16	SiO ₂	95.32283	40	SiO ₂	225.0774
17	Si:H	68.92315	41	Si:H	32.91478
18	SiO ₂	96.5938	42	SiO ₂	284.8275
19	Si:H	126.1687	43	Si:H	90.36095
20	SiO ₂	66.16271	44	SiO ₂	79.30571
21	Si:H	88.58283	45	Si:H	55.39493
22	SiO ₂	96.5938	46	SiO ₂	247.4205
23	Si:H	63.19303	47	Si:H	95.3999
24	SiO ₂	103.7141	48	SiO ₂	285.9541

FIG. 7C

**FIG. 7D****FIG. 7E**

Comparison of Second Conventional Optical Filter and Second Exemplary Optical Filter		
Property	Second Conventional Optical Filter	Second Exemplary Optical Filter
FWHM (nm)	29.1	29.6
Center-wavelength shift, 0° to 20° (nm)	-12.7	-7.8
Background transmittance for 2856 K blackbody (%)	5.84	5.54
Total coating thickness (nm)	13780	3312

FIG. 8A

Filter Stack of Second Exemplary Optical Filter					
Layer No.	Material	Thickness (nm)	Layer No.	Material	Thickness (nm)
1	SiO ₂	169.8593	14	Si:H	42.95783
2	Si:H	25.36196	15	SiO ₂	151.3625
3	SiO ₂	169.8593	16	Si:H	108.6165
4	Si:H	108.6165	17	SiO ₂	141.1964
5	SiO ₂	141.1964	18	Si:H	54.30826
6	Si:H	54.30826	19	SiO ₂	173.3892
7	SiO ₂	173.3892	20	Si:H	22.70085
8	Si:H	22.70085	21	SiO ₂	173.3892
9	SiO ₂	173.3892	22	Si:H	108.6165
10	Si:H	108.6165	23	SiO ₂	155.1748
11	SiO ₂	141.1964	24	Si:H	38.8304
12	Si:H	54.30826	25	SiO ₂	155.1748
13	SiO ₂	151.3625			

FIG. 8B

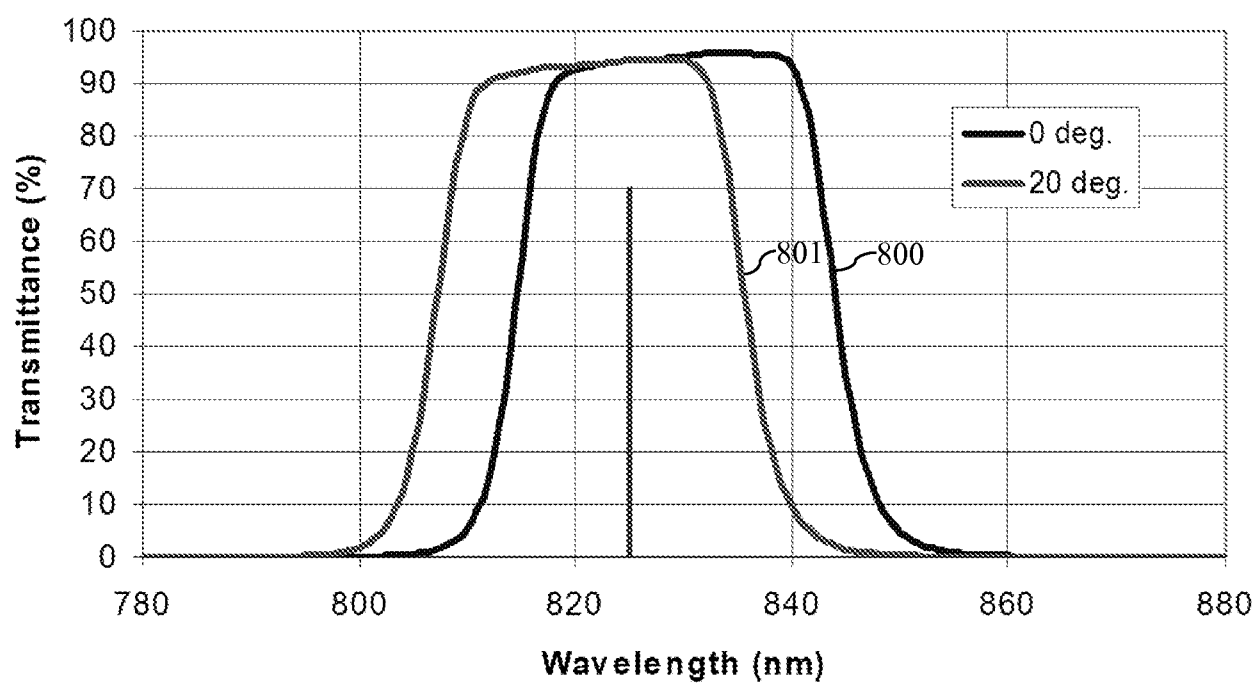


FIG. 8C

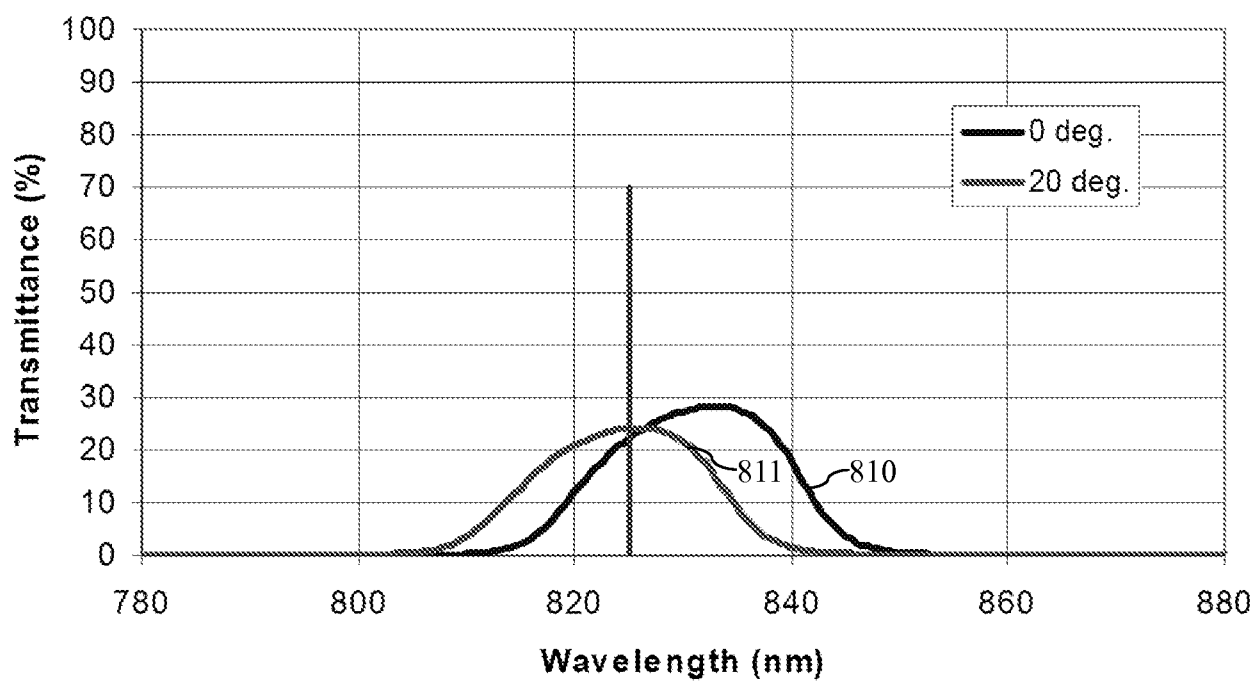
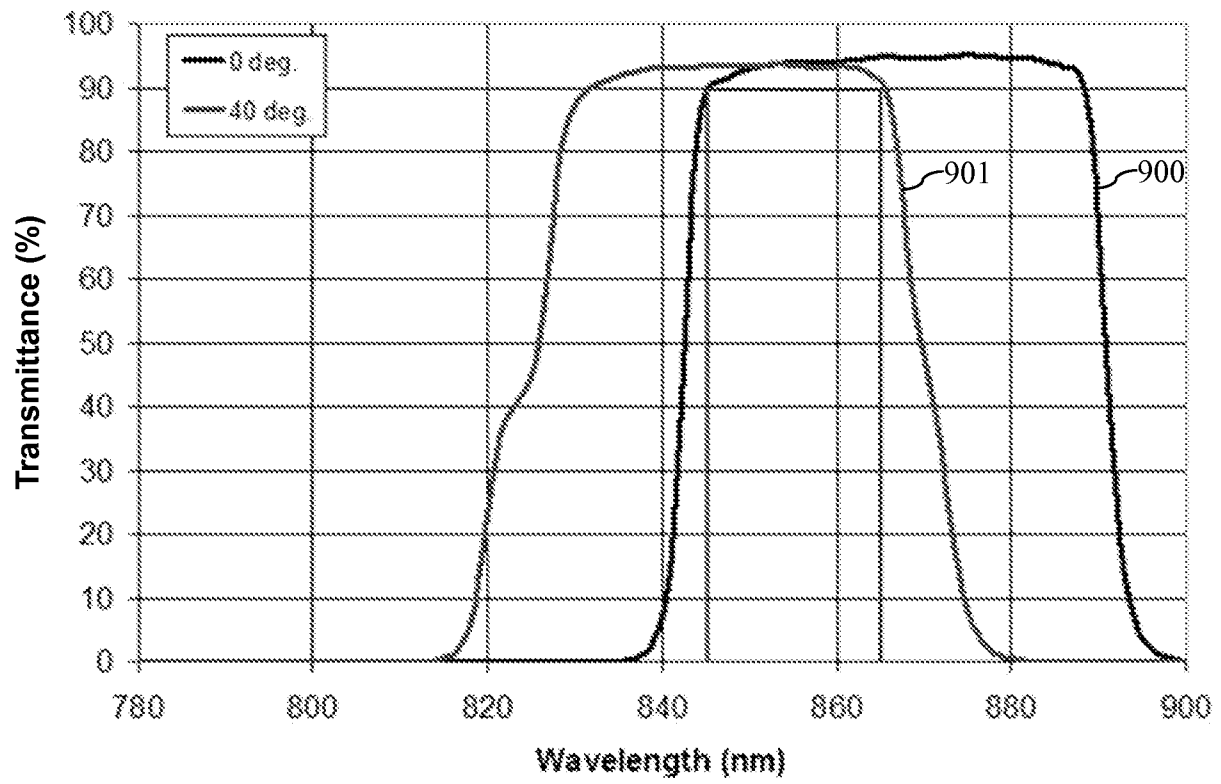
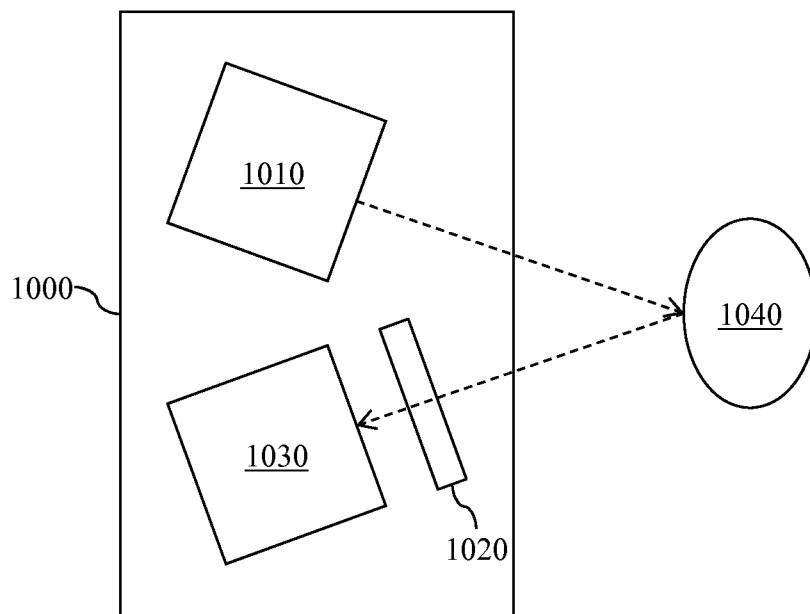


FIG. 8D

Filter Stack of Third Exemplary Optical Filter					
Layer No.	Material	Thickness (nm)	Layer No.	Material	Thickness (nm)
1	Si:H	48.99656	16	SiO ₂	144.9036
2	SiO ₂	27.72806	17	Si:H	172.5048
3	Si:H	261.865	18	SiO ₂	144.8237
4	SiO ₂	175.7108	19	Si:H	229.229
5	Si:H	67.55759	20	SiO ₂	131.8658
6	SiO ₂	48.09467	21	Si:H	77.24942
7	Si:H	245.3538	22	SiO ₂	139.1643
8	SiO ₂	157.5898	23	Si:H	225.9625
9	Si:H	53.78669	24	SiO ₂	115.736
10	SiO ₂	117.5423	25	Si:H	97.86642
11	Si:H	234.1488	26	SiO ₂	170.7001
12	SiO ₂	146.2907	27	Si:H	232.4637
13	Si:H	172.8534	28	SiO ₂	168.9233
14	SiO ₂	143.1595	29	Si:H	118.3322
15	Si:H	230.0482			

FIG. 9A

**FIG. 9B**

**FIG. 10**

600

